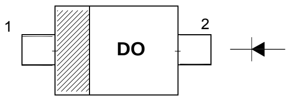
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- Super-high speed switching circuit
- Small current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: **"DO"**
Simplified outline SOD-323 and symbol

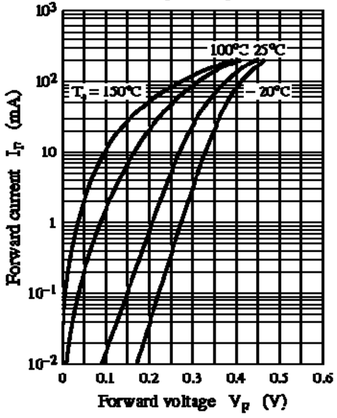
Absolute Maximum Ratings (T_a = 25 °C)

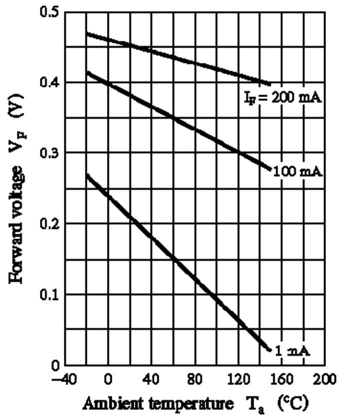
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Forward Current	I_{FM}	300	mA
Average Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current 1)	I_{FSM}	1	A
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

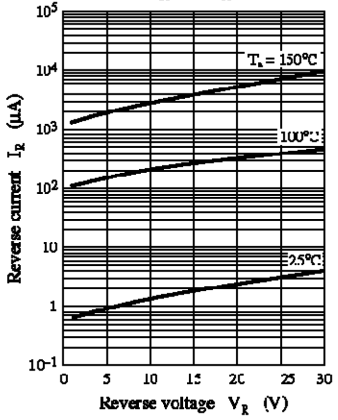
1) The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

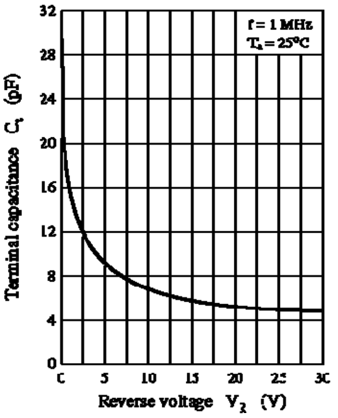
Characteristics at T_a = 25 °C

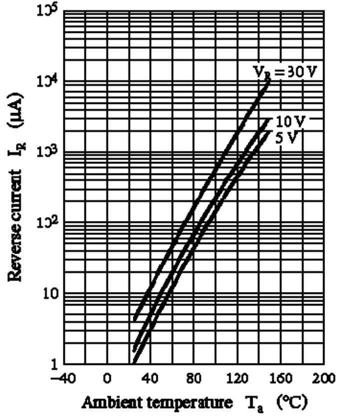
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 200 mA	V_F	-	0.55	V
Reverse Current at V_R = 30 V	I_R	-	50	µA
Terminal Capacitance at f = 1 MHz	C_T	30	-	pF
Reverse Recovery Time at $I_F = I_R$ = 100 mA, I_{rr} = 10 mA, R_L = 100 Ω	t_{rr}	3	-	ns


I_F — V_F


V_F — T_a


I_R — V_R


C_t — V_R


I_R — T_a